



sPHENIX INTT

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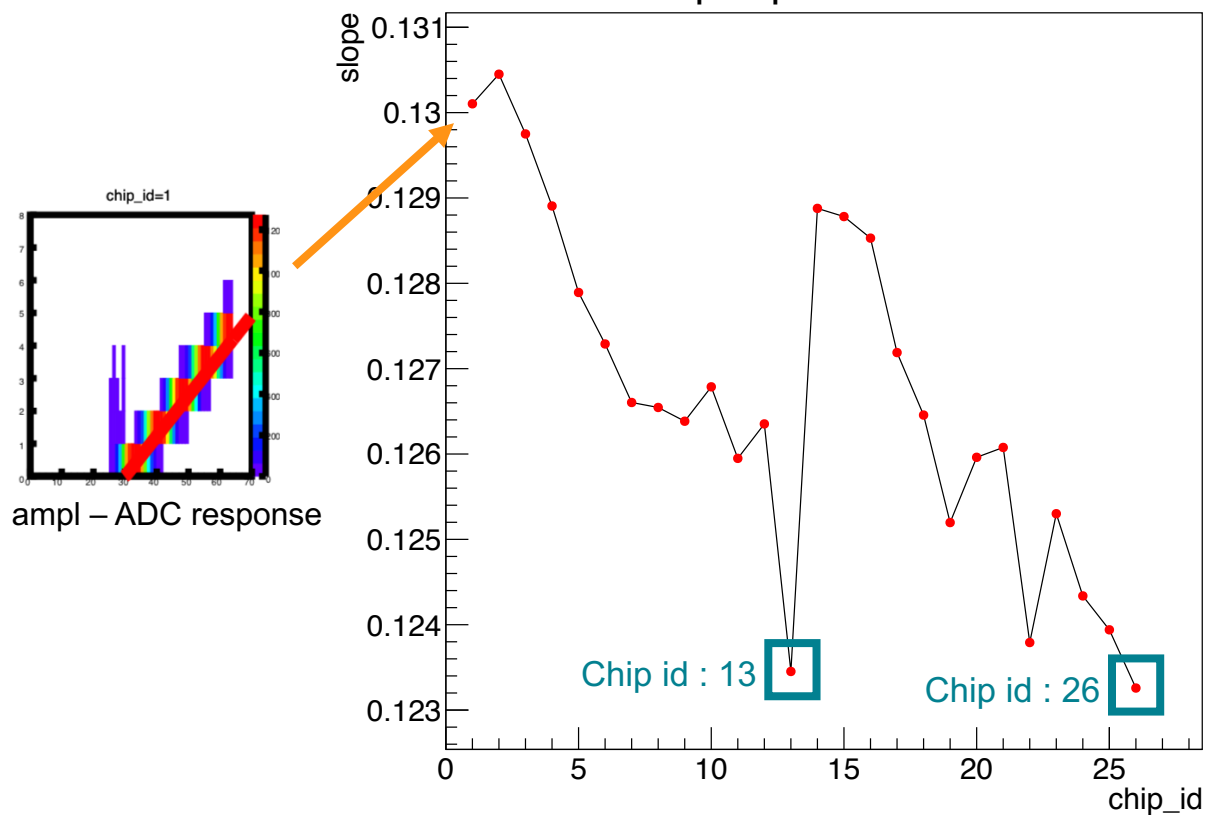
Rachid Nouicer (BNL)



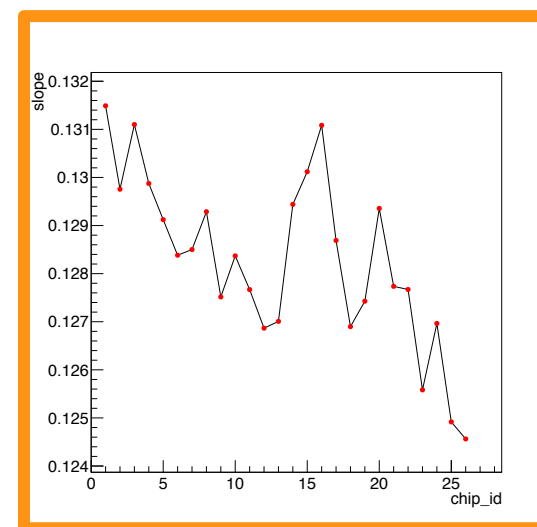
Chip ID to slope



INTT pre-production 001



FVTX result

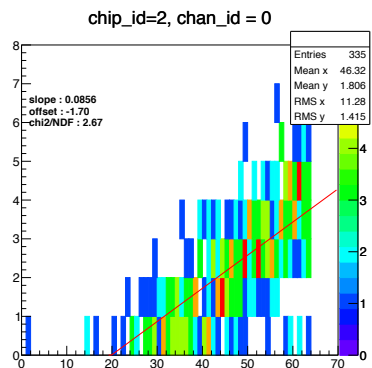




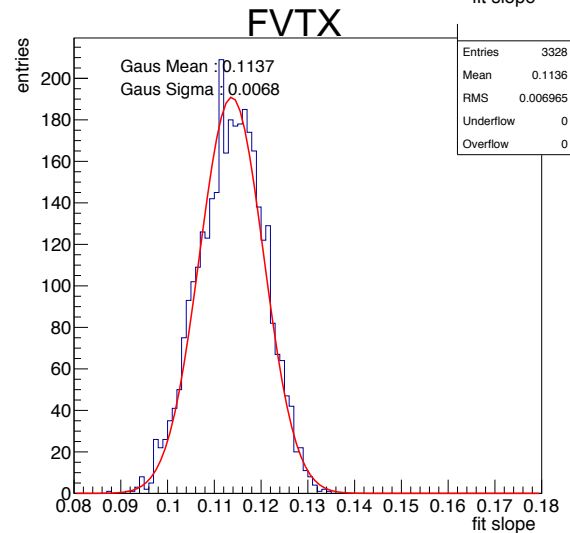
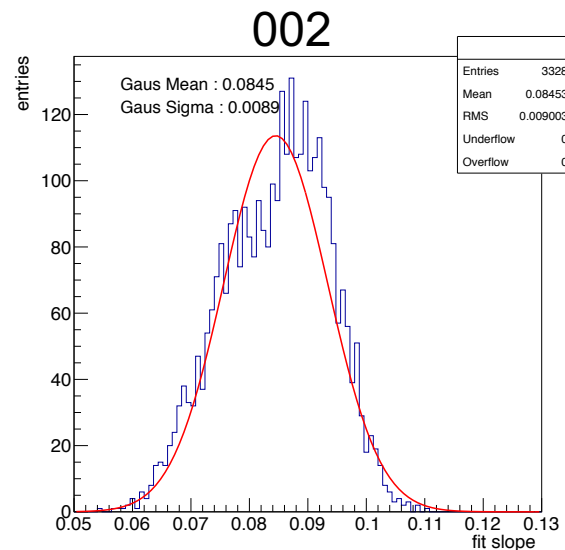
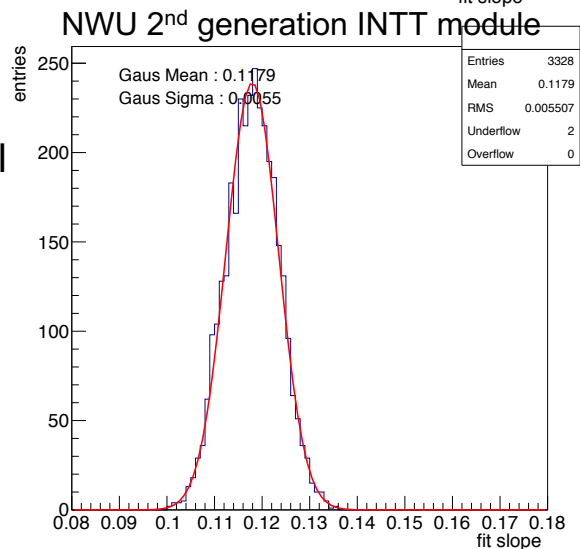
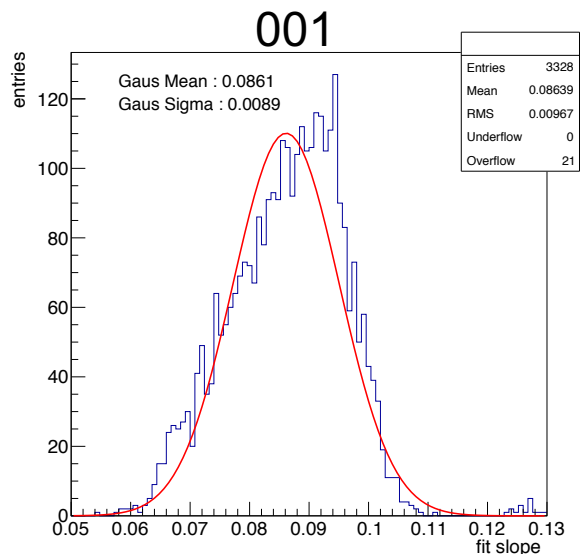
INTT module performance check SPHENIX



Without bias voltage



The slope of each channel

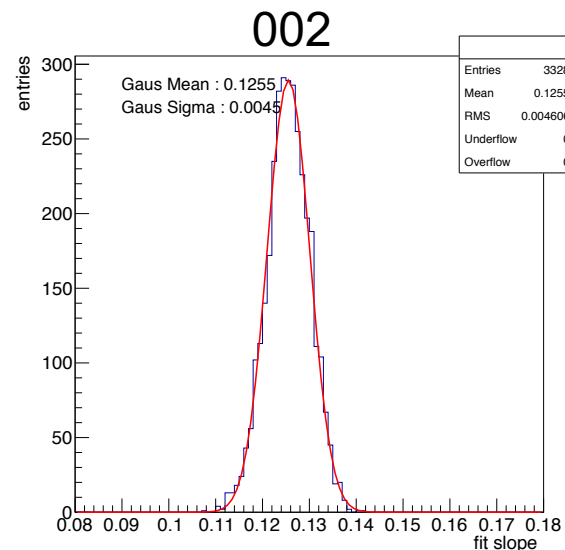
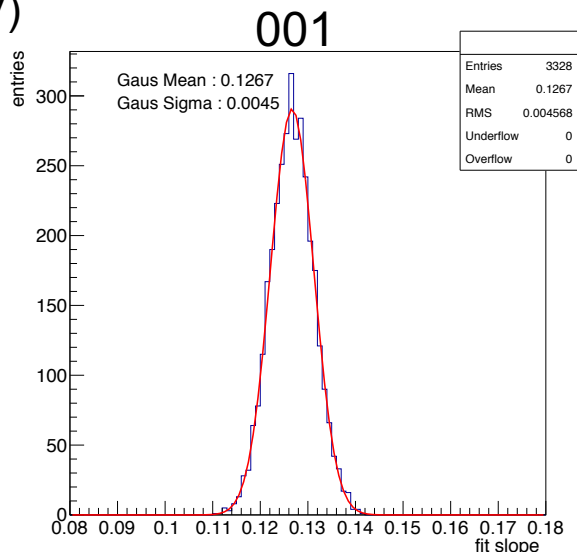




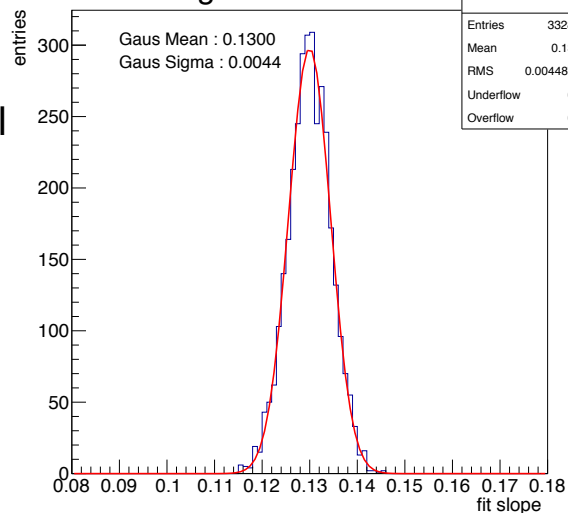
INTT module performance check



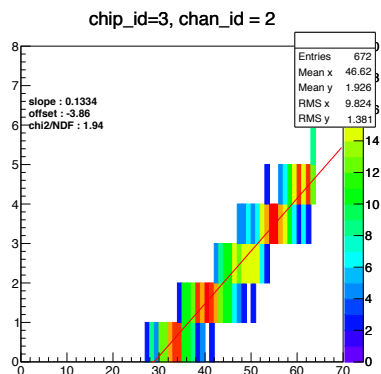
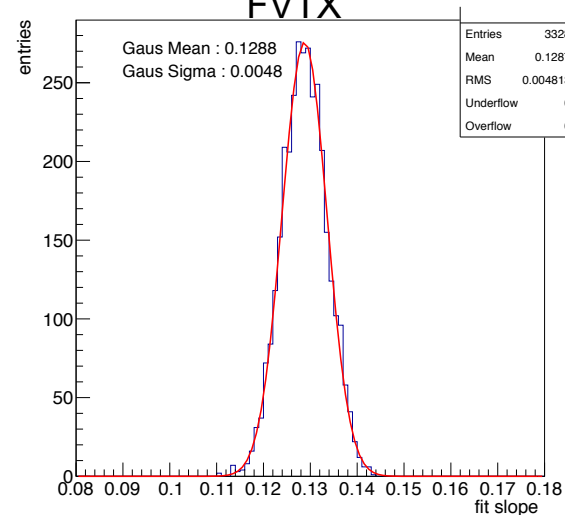
With bias voltage (+50V)



NWU 2nd generation INTT module



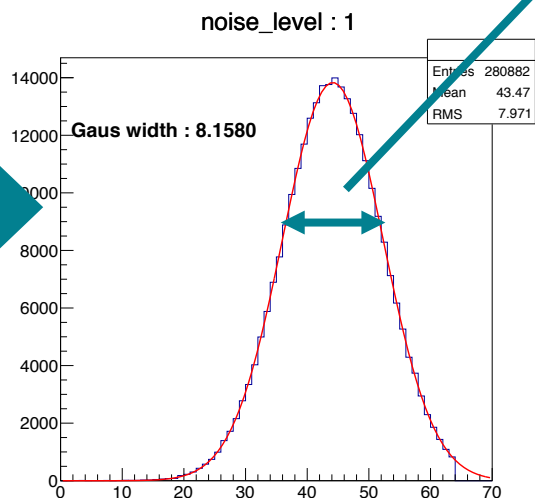
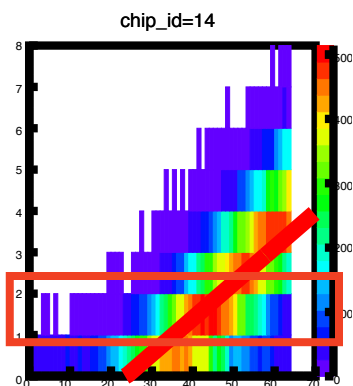
FVTX



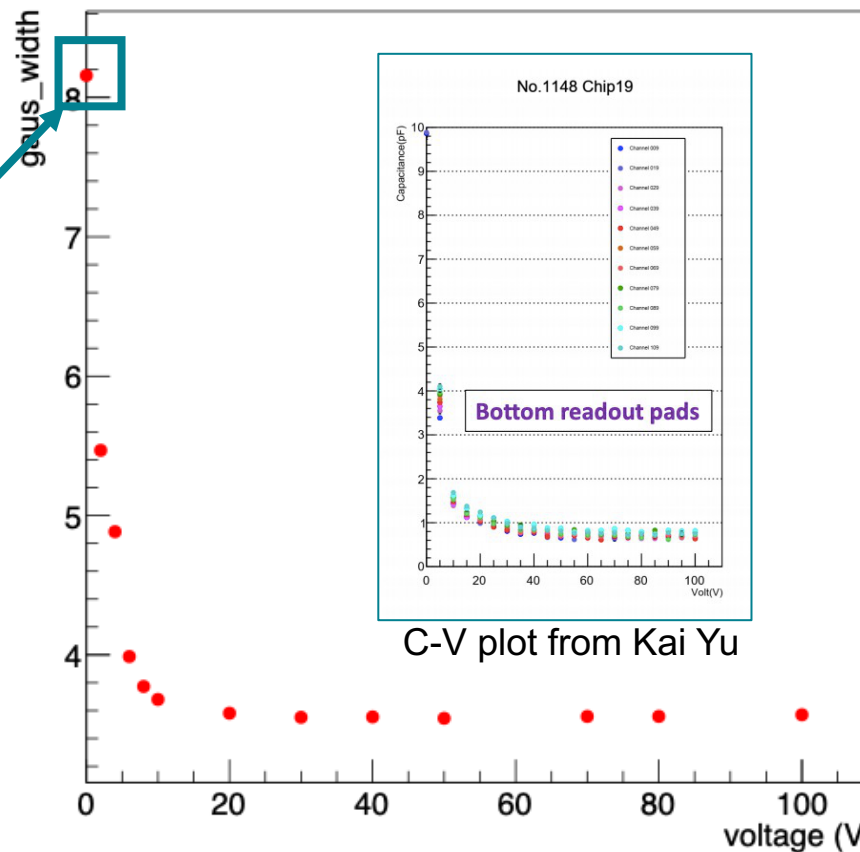
The slope of each channel



Noise level test



pre-Production-002, gaus_width to V





To do list



- R&D the encapsulated glue apply.
- Pedestal test
- Cosmic ray test
- Source test

- Modify the assembly tools -> massive production
 - Re-arrangement of gantry table space
 - Module pick and place exercise

Back up



INTT module performance check SPHENIX

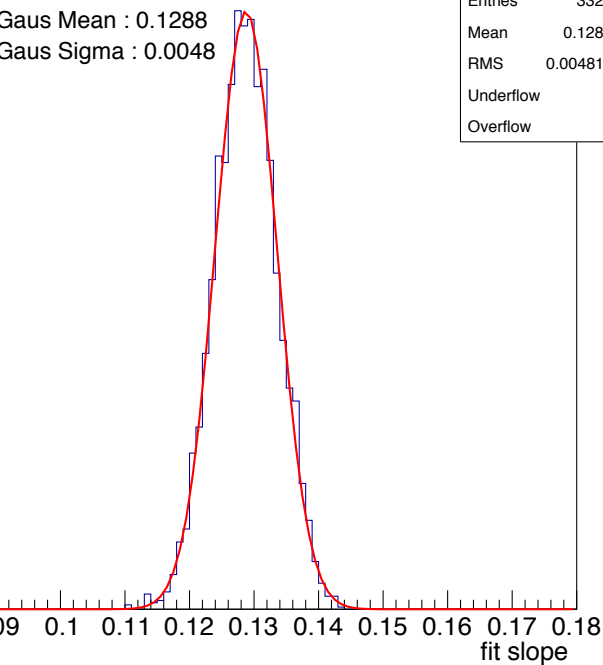


With bias voltage (+50V)

FVTX

Gaus Mean : 0.1288
Gaus Sigma : 0.0048

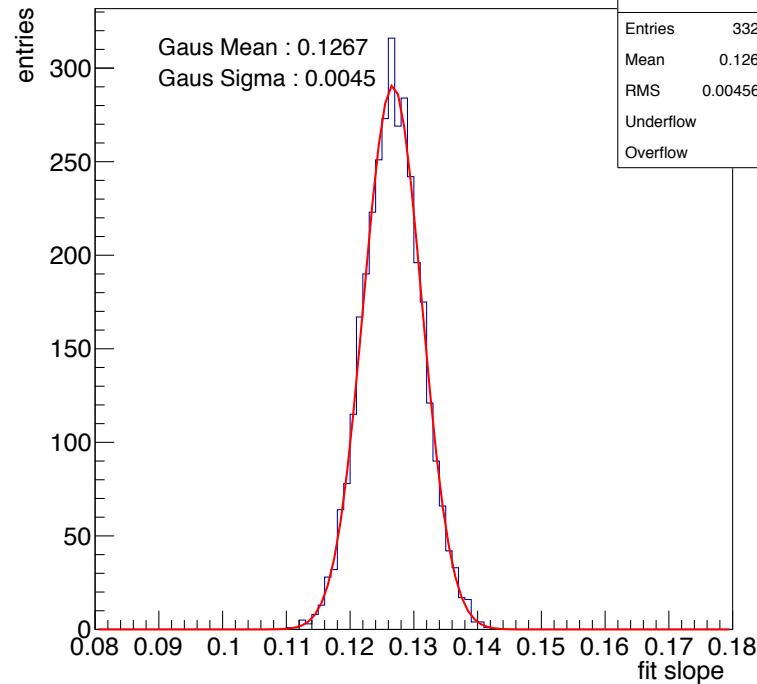
Entries	3328
Mean	0.1287
RMS	0.004813
Underflow	0
Overflow	0



001

Gaus Mean : 0.1267
Gaus Sigma : 0.0045

Entries	3328
Mean	0.1267
RMS	0.004568
Underflow	0
Overflow	0



002

Gaus Mean : 0.1255
Gaus Sigma : 0.0045

